

ABSTRACT OF THE DISCLOSURE

An electrode structure on a p-type III group nitride semiconductor layer includes first, second and third electrode layers successively stacked on the semiconductor layer. The first electrode layer includes at least one
5 selected from a first metal group of Ti, Hf, Zr, V, Nb, Ta, Cr, W and Sc. The second electrode layer includes at least one selected from a second metal group of Ni, Pd and Co. The third electrode layer includes Au.

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